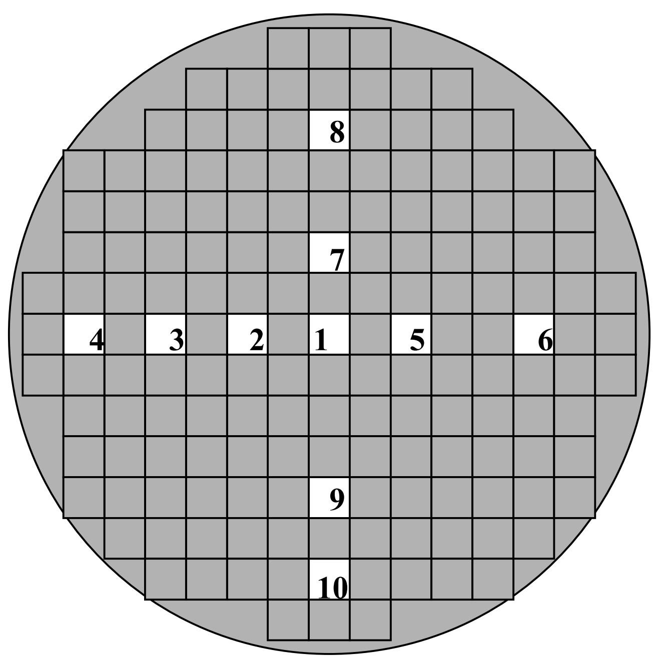
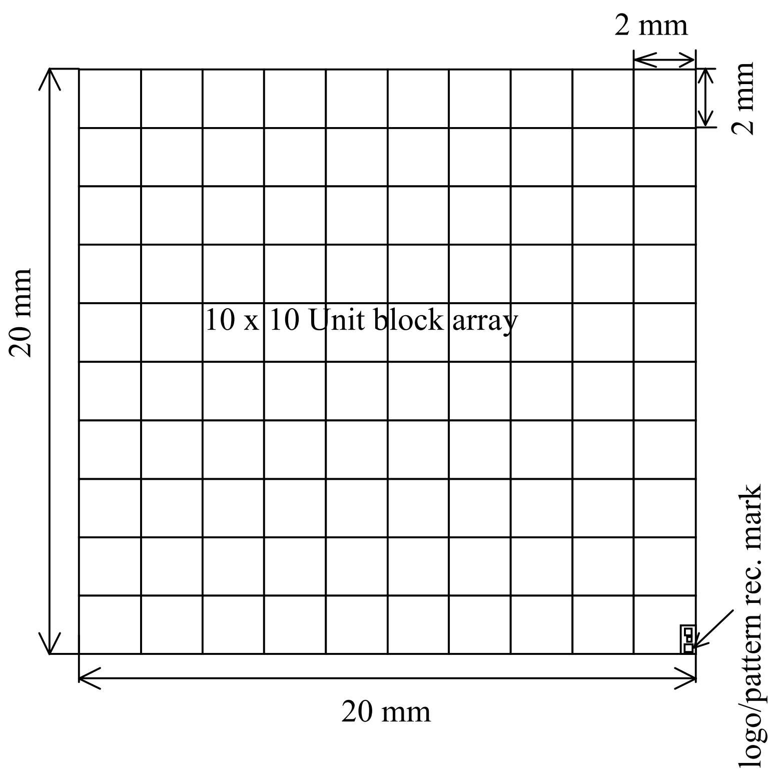
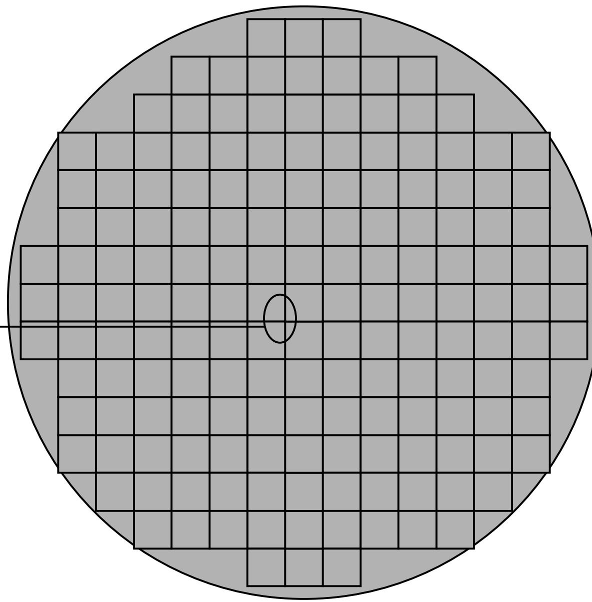
Standard Pre- and Post-CMP Oxide Thickness Measurement Plan

(Type: SKW 3-5, 300mm, 10 dies/wafer)



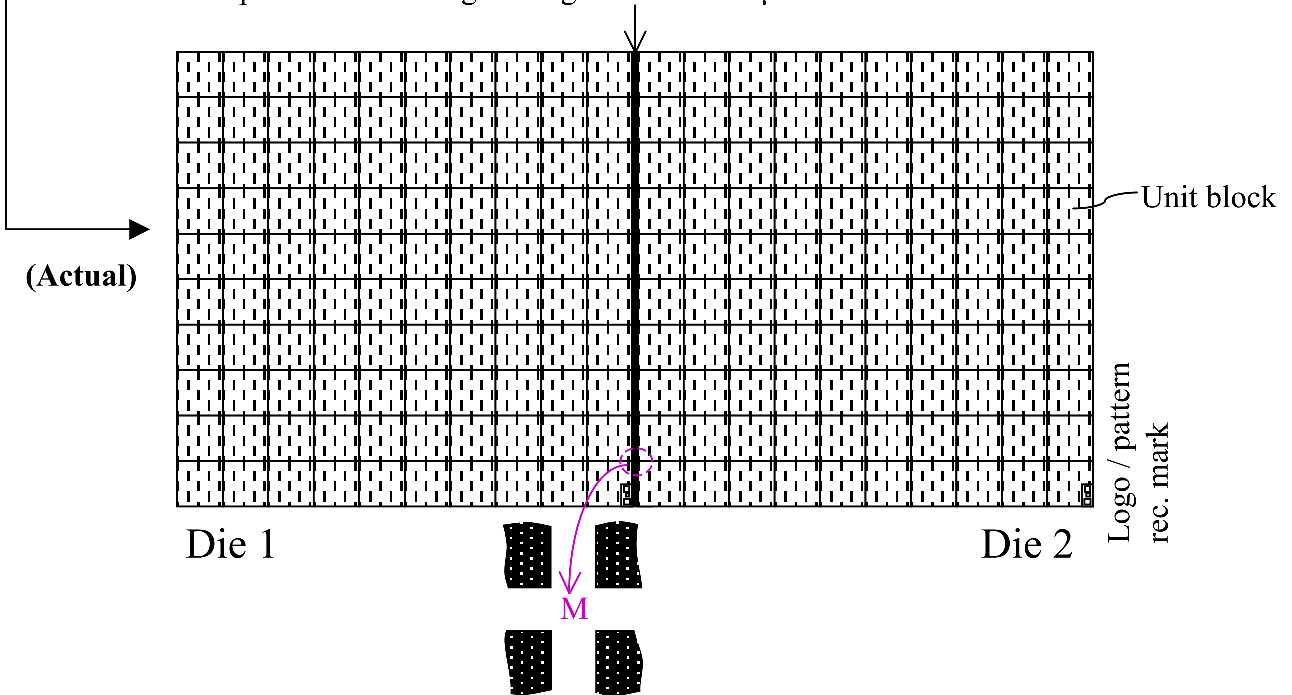


SKW 3-5 Mask Floor Plan



8 inch wafers are patterned using this mask, and the resulting wafer cross sectional view is shown in the previous figure. As indicated, the corresponding patterns are generated by etching SiN CMP stopper / SiO2 oxide / Si substrate and then filling the trench with HDP SiO2.

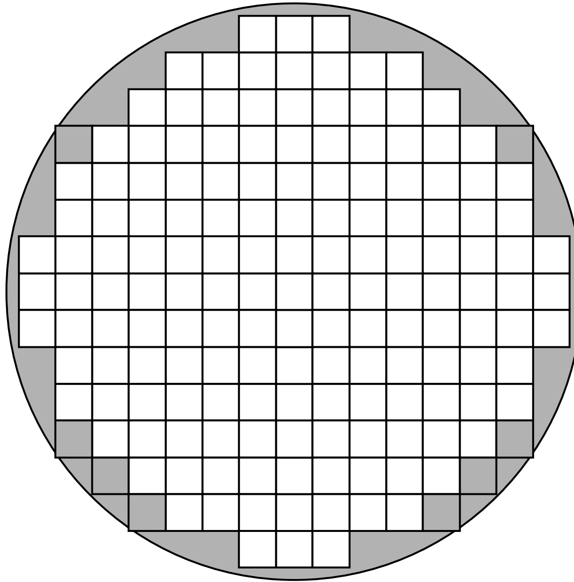
The space between neighboring two dies is 20μm.

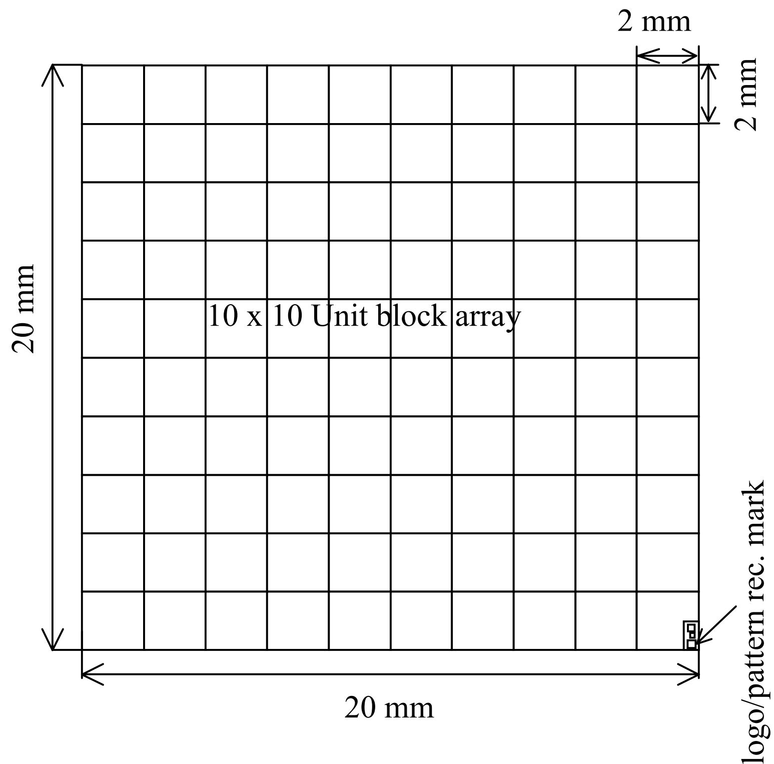


M: Recommended film thickness monitoring site (60 X 60 μm)

Pre- and Post-CMP Defect Characterization Plan

(Type: SKW 3-5, 300mm, all full dies)





SKW 3-5 Mask Floor Plan